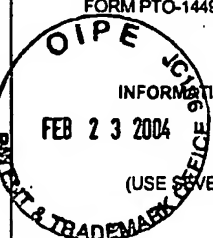


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	FILING DATE June 19, 2003	GROUP ART UNIT 2811

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CK	1. Chatterjee et al., "CMOS Metal Replacement Gate Transistors using Tantalum Pentoxide Gate Insulator," IEEE, IEDM, 0-7803-4774-9/98, pp. 777-780 (1998)
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CK	4. Ferguson et al., "Titanium Nitride Metal Gate Electrode: Effect of Nitrogen Incorporation," Advanced Metallization Conference 2001 (AMC 2001), pp. 115-119
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CK	8. Polishchuk, "Dual Work Function Metal Gate CMOS Technology Using Metal Interdiffusion," IEEE Electron Device Letter, Vol. 22, No. 9 pp. 444-446 (2001)
CK	9. Wakabayashi et al., "A Novel W/TiNx Metal Gate CMOS Technology using Nitrogen-Concentration-Controlling TiNx Film," IEEE, IEDM, 0-7803-5410-9/99, pp. 253-256 (1999)
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CK	13. Zhong et al., "Electrical Properties of RuO <sub>2</sub> Gate Electrodes for Dual Metal Gate Si-CMOS," IEEE Electron Device Letters, Vol. 21, No. 12, December 2000, pp. 593-595

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